Semiconductor Device Set - Page 1 of 1



current megawatts all

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Inclosure	Material:
Metal all tra	ansistor
Overall Le	ngth:
0.170 inche	es all transistor and 0.210 inches all transistor
Terminal L	_ength:
0.500 inche	es all transistor
Overall Dia	ameter:
0.209 inche	es all transistor and 0.230 inches all transistor
Internal Co	onfiguration:
Field effect	all transistor
Channel P	olarity And Control Type (non-core):
N-channel	junction type all transistor
Joint Elec	tronic Device Engineering Council/jedec/case Outline Designation:
To-72 all tr	ansistor
Compone	nt Function Relationship:
Matched	
Compone	nt Name And Quantity:
2 transisto	
Mounting	Method:
Terminal a	Il transistor
Terminal (	Circle Diameter:
0.100 inche	es all transistor
Features F	Provided:
Hermetical	ly sealed case
Semicond	uctor Material:
Silicon all t	ransistor
Voltage Ra	ating In Volts Per Characteristic:
10.0 drain	to source voltage all transistor
Current Ra	ating Per Characteristic:
10.00 millia	amperes operating voltage megawatts all transistor and 30.00 milliamperes zero-gate-voltage source of
transistor	
Power Rat	ing Per Characteristic:
300.0 milliv	vatts small-signal input power, common-collector absolute all transistor
Terminal 1	Type And Quantity:
4 uninsulat	ed wire lead all transistor
Shelf Life:	
N/a	
Unit Of Me	easure:
 Demilitariz	zation:
No	
Fiig:	
A110a0	